

2SK1297

Silicon N-Channel MOS FET

HITACHI

November 1996

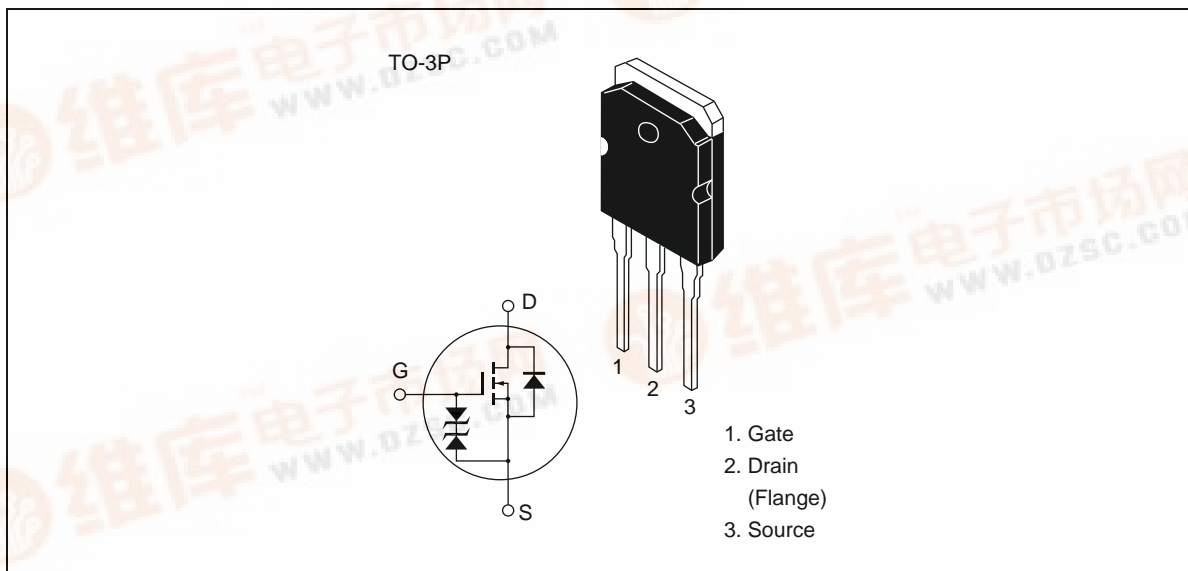
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



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Absolute Maximum Ratings (Ta = 25°C)

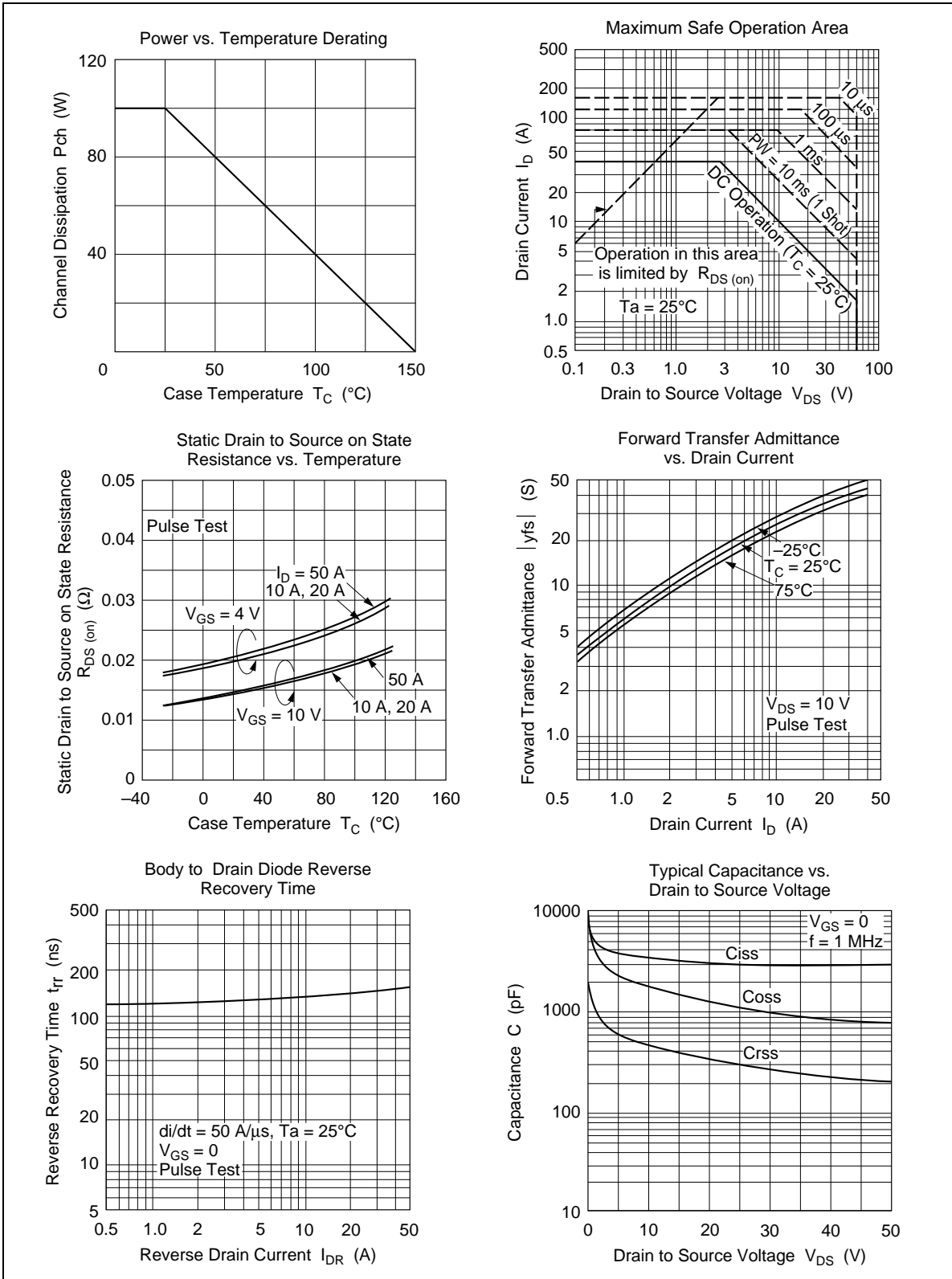
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	40	A
Drain peak current	$I_{D(pulse)}^{*1}$	160	A
Body to drain diode reverse drain current	I_{DR}	40	A
Channel dissipation	Pch^{*2}	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

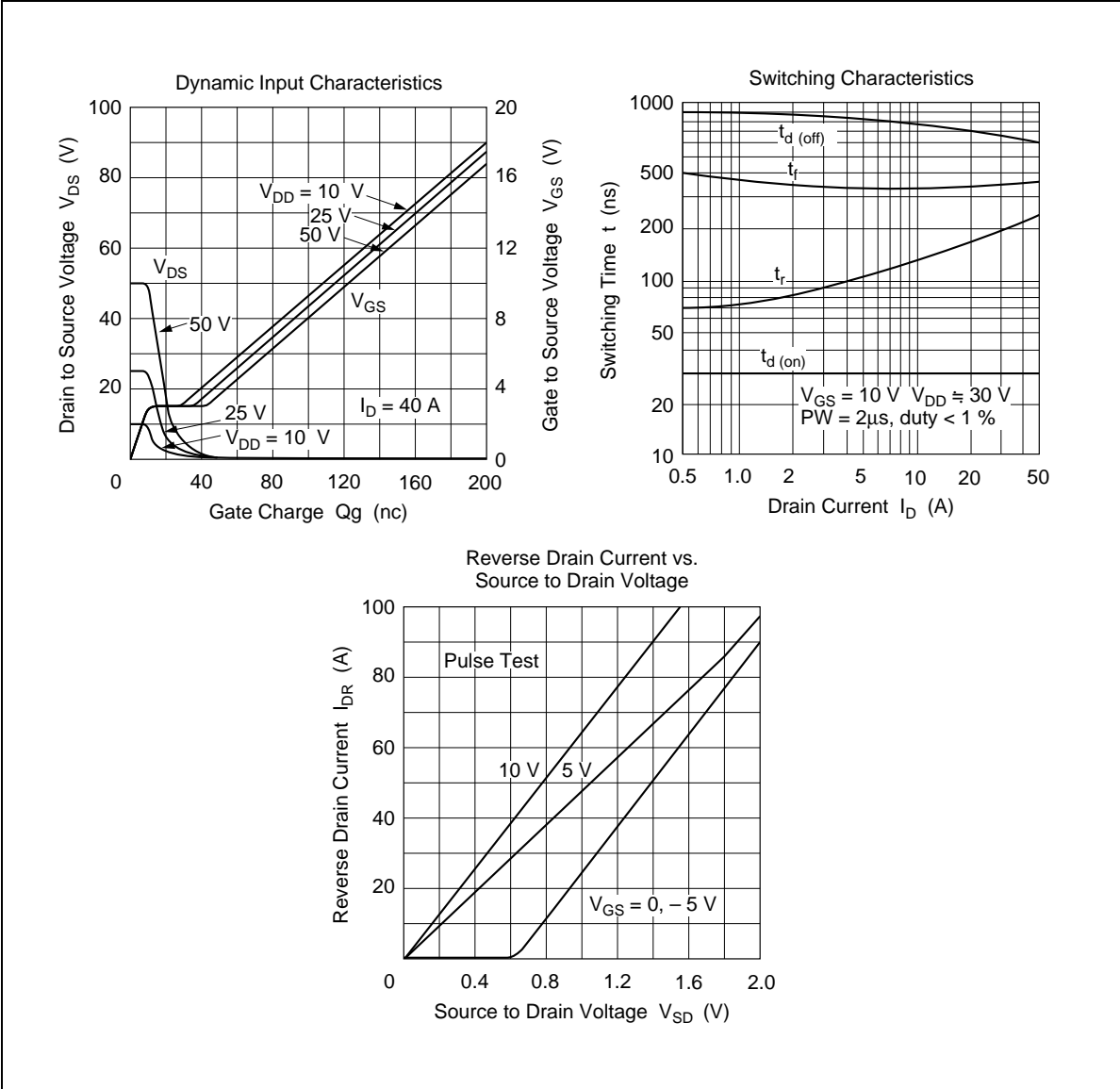
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

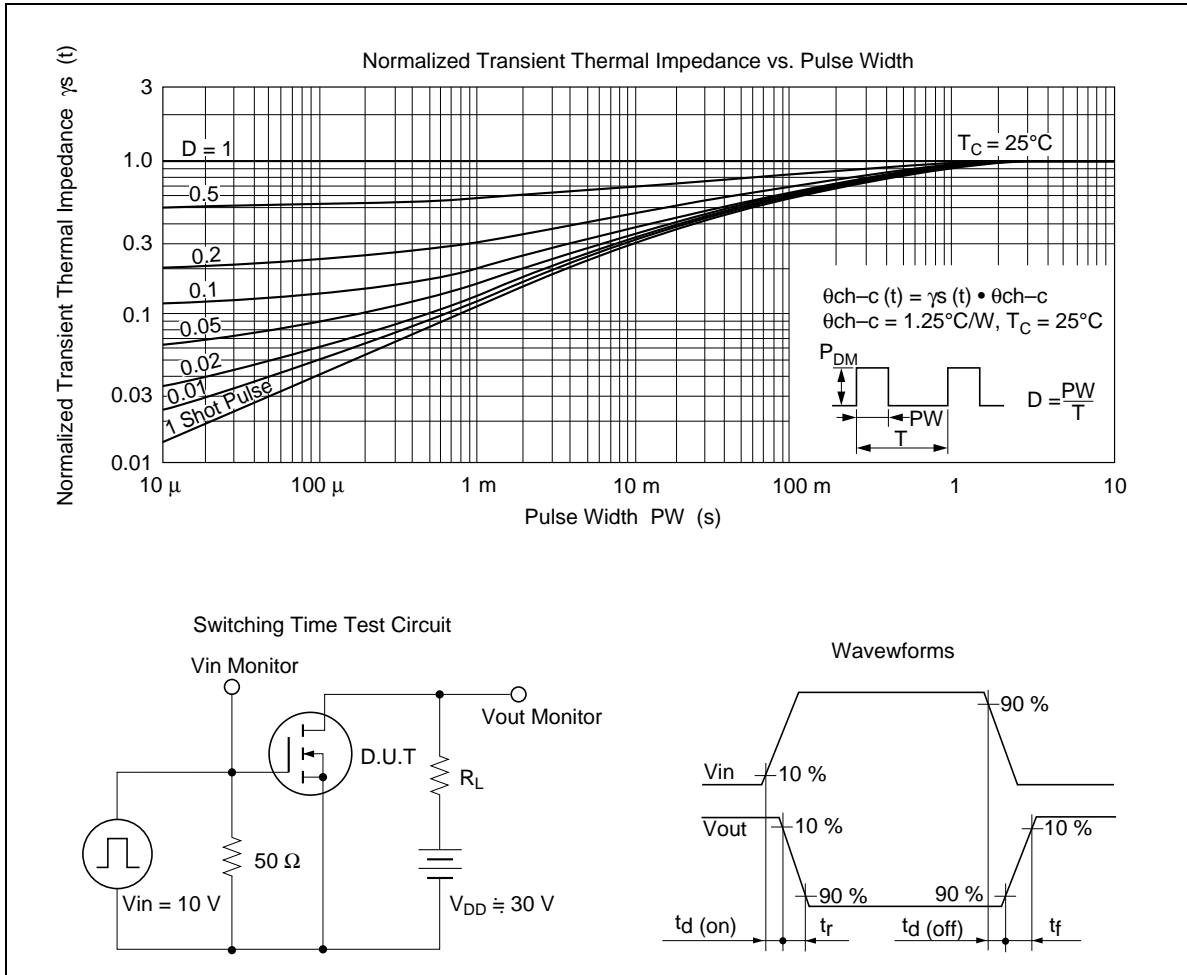
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10\text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\ \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 50\text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1\text{ mA}, V_{DS} = 10\text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.015	0.018	Ω	$I_D = 20\text{ A}, V_{GS} = 10\text{ V}^{*1}$
		—	0.02	0.025	Ω	$I_D = 20\text{ A}, V_{GS} = 4\text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	22	35	—	S	$I_D = 20\text{ A}, V_{DS} = 10\text{ V}^{*1}$
Input capacitance	C_{iss}	—	3600	—	pF	$V_{DS} = 10\text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	1850	—	pF	$f = 1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	450	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 20\text{ A}, V_{GS} = 10\text{ V},$
Rise time	t_r	—	170	—	ns	$R_L = 1.5\ \Omega$
Turn-off delay time	$t_{d(off)}$	—	700	—	ns	
Fall time	t_f	—	350	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.2	—	V	$I_F = 40\text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	155	—	ns	$I_F = 40\text{ A}, V_{GS} = 0,$ $di_F/dt = 50\text{ A}/\mu\text{s}$

Note 1. Pulse test







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